

JM38510/13503LOW-NOISE PRECISION
OPERATIONAL AMPLIFIER

Precision Monolithics Inc.

T-79-06-10

FEATURES

- Low V_{OS} $25\mu V$
- Low V_{OS} Drift $0.6\mu V/\text{°C}$
- High Speed $1.7V/\mu s$
- Low Noise $0.18\mu V_{\text{p-p}}$
- High Gain 1.0 Million
- Wide Supply Voltage Range $\pm 4.5V$ to $\pm 18V$

ORDERING INFORMATION

JAN SLASH SHEET	PMI DEVICE
JM38510/13503BGC	OP27AJ1/38510
JM38510/13503BGA	OP27AJ5/38510
JM38510/13503SGA	OP27SAJ5/38510
JM38510/13503BPB	OP27AZ2/38510
JM38510/13503BPA	OP27AZ5/38510
JM38510/13503SPA	OP27SAJ5/38510

GENERAL DESCRIPTION

This data sheet covers the electrical requirements for a monolithic, low offset voltage, internally-compensated operational amplifier as specified in MIL-M-38510/135 for device type 03. Devices supplied to this data sheet are manufactured and tested at PMI's MIL-M-38510 certified facility and are listed in QPL-38510.

Complete device requirements will be found in MIL-M-38510 and MIL-M-38510/135 for Class B and Class S processed devices.

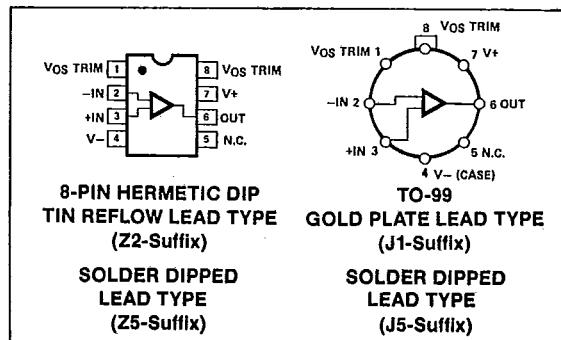
GENERIC CROSS-REFERENCE INFORMATION

This cross-reference information is presented for the convenience of the user. The generic-industry types listed may not have identical operational performance characteristics across the military

temperature range or reliability factors equivalent to the MIL-M-38510 device.

MILITARY DEVICE TYPE	GENERIC-INDUSTRY TYPE
03	OP27A

For an 833-processed device with improved electrical specifications, review the OP-27 data sheet.

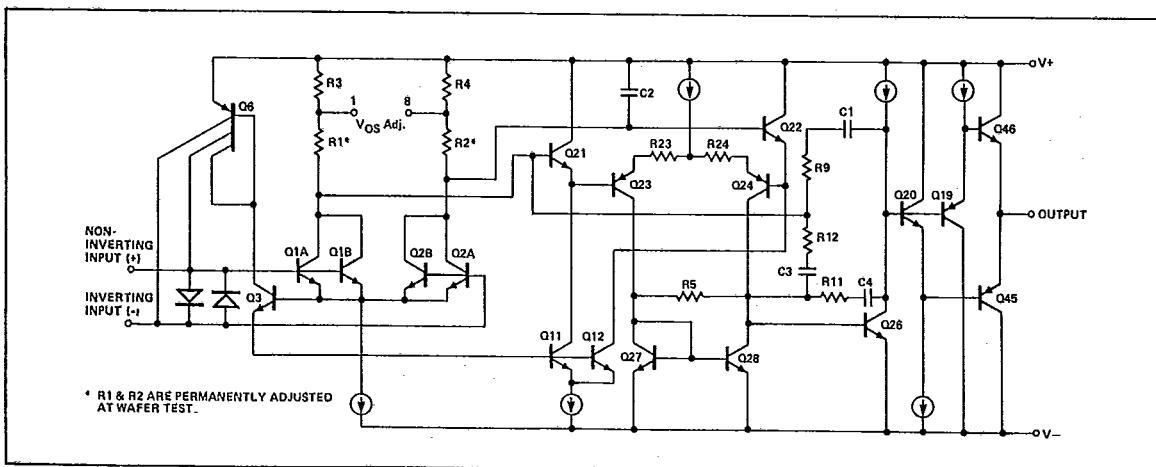
PIN CONNECTIONS

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OPERATIONAL AMPLIFIERS/BUFFERS

POWER AND THERMAL CHARACTERISTICS

Case Outline	Package	Maximum Allowable Power Dissipation	θ_{JC}	θ_{JA}
P	Dual-In-Line	208mW @ $T_A = 125^\circ C$	$50^\circ C/W$	$120^\circ C/W$
G	8-Lead CAN	167mW @ $T_A = 125^\circ C$	$40^\circ C/W$	$150^\circ C/W$

SIMPLIFIED SCHEMATIC

ABSOLUTE MAXIMUM RATINGS

Supply Voltage (V_{CC})	$\pm 22V$
Input Voltage Range (V_{IN})	$\pm V_{CC}$
Differential Input Voltage Range	$\pm 0.7V$
Output Short-Circuit Duration (Note 1)	
Lead Temperature (Soldering, 60 sec)	+300°C
Storage Temperature Range	-65°C to +150°C
Junction Temperature (T_J)	+150°C
Maximum Power Dissipation (P_D) (Note 2)	500mW

RECOMMENDED OPERATING CONDITIONS

Supply Voltage Range	$\pm 4.5V$ to $\pm 18V$
Ambient Temperature Range	-55°C to +125°C

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NOTES:

1. Output may be shorted to ground indefinitely at $V_S = \pm 15V$, $T_A = 25^\circ C$. Temperature and/or supply voltages must be limited to ensure dissipation rating is not exceeded.
2. Maximum power dissipation versus ambient temperature.

ELECTRICAL CHARACTERISTICS at $\pm 4.5V \leq V_{CC} \leq \pm 20V$ and $-55^\circ C \leq T_A \leq 125^\circ C$, $R_S = 50\Omega$ unnullled, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	03 LIMITS		UNITS
			MIN	MAX	
Input Offset Voltage	V_{IO}	$T_A = 25^\circ C$ (Notes 1, 2)	-26 -60	25 60	μV
Input Offset Voltage Temperature Sensitivity	$\Delta V_{IO}/\Delta T$	(Note 1)	-0.6	0.6	$\mu V/^\circ C$
Input Bias Current	$+I_{IB}$	$T_A = 25^\circ C$ (Note 1)	-40 -60	40 60	nA
	$-I_{IB}$	$T_A = 25^\circ C$ (Note 1)	-40 -60	40 60	nA
Input Offset Current	I_{IO}	$T_A = 25^\circ C$ (Note 1)	-35 -50	35 50	nA
Power Supply Rejection Ratio	+PSRR	$+V_{CC} = 18V$ to $5V$, $-V_{CC} = -15V$ $T_A = 25^\circ C$	—	10	
	-PSRR	$+V_{CC} = 15V$, $-V_{CC} = -18V$ to $-5V$ $T_A = 25^\circ C$	—	10	
	+PSRR	$+V_{CC} = 18V$ to $5V$, $-V_{CC} = -15V$	—	16	$\mu V/V$
	-PSRR	$+V_{CC} = 15V$, $-V_{CC} = -18V$ to $-5V$	—	16	
PSRR		$V_{CC} = \pm 4.5V$ to $\pm 18V$ $T_A = 25^\circ C$	—	10	
		$V_{CC} = \pm 4.5V$ to $\pm 18V$	—	16	

NOTES:

1. Tested at $V_{CM} = 0$, $V_{CC} = \pm 15V$.
2. Due to the inherent warm-up drift, testing shall occur no sooner than three (3) minutes after application of power.

ELECTRICAL CHARACTERISTICS at $\pm 4.5V \leq V_{CC} \leq \pm 20V$ and $-55^{\circ}C \leq T_A \leq +125^{\circ}C$, $R_S = 50\Omega$ unnullled, unless otherwise noted. *Continued*

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PARAMETER	SYMBOL	CONDITIONS	03 LIMITS		UNITS
			MIN	MAX	
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 11V, T_A = +25^{\circ}C, V_{CC} = \pm 15V$ $V_{CM} = \pm 10V, V_{CC} = \pm 15V$	114 108	— —	dB
Adjustment for Input Offset	V_{IO} Adj (+) V_{IO} Adj (-)	$T_A = +25^{\circ}C$, (Note 1) $T_A = +25^{\circ}C$, (Note 1)	0.5 —	— -0.5	mV
Output Short-Circuit Current	$I_{OS(+)}$ $I_{OS(-)}$	$t \leq 25ms$, (Notes 1,3) $t \leq 25ms$, (Notes 1,3)	-70 —	— 70	mA
Supply Current	I_{CC}	$T_A = +25^{\circ}C$ (Note 1)	— —	5 6	mA
Output Voltage Swing (Minimum)	V_{OP}	$R_L = 600\Omega$, (Note 1) $R_L = 2k\Omega$, (Note 1)	-10 -11.5	10 11.5	V
Open Loop Voltage Gain (Single Ended)	A_{VS}	$T_A = +25^{\circ}C$ (Note 2)	1000 600	— —	V/mV
Slew Rate	SR(+), SR(-)	$V_{IN} = 10V, T_A = +25^{\circ}C$, (Note 1)	1.7	—	V/ μ s
Input Noise Voltage Density	e_n	$f_O = 10Hz$ $f_O = 100Hz \quad TA = +25^{\circ}C$, (Note 1) $f_O = 1kHz$	— — —	5.5 4.0 3.8	nV/ \sqrt{Hz}
Low Frequency Input Noise Voltage	e_{np-p}	$f = 0.1Hz$ to $10Hz$ $T_A = +25^{\circ}C$, (Note 1)	—	0.18	μ V _{p-p}
Input Noise Current Density	i_n	$f_O = 10Hz$ $f_O = 100Hz \quad TA = +25^{\circ}C$, (Note 1) $f_O = 1kHz$	— — —	5.66 1.88 0.84	pA/ \sqrt{Hz}

NOTES:

1. Tested at $V_{CM} = 0, V_{CC} = \pm 15V$.
2. $V_{OUT} = 0$ to $+10$ for $A_{VS}(+)$ and $V_{OUT} = 0$ to $-10V$ for $A_{VS}(-)$. $R_L = 2,000\Omega$.
3. Continuous short-circuit limits are considerably less than the indicated test limits, since maximum power dissipation cannot be exceeded.

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